

## Product Overview

### NGTB40N120IHR: IGBT, 1200V 40A FS2-RC Induction Heating

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on-state voltage and minimal switching loss. The IGBT is well suited for resonant or soft switching applications.

#### Features

- Optimized for Low Case Temperature in IH Cooker Applications
- Extremely Efficient Trench with Fieldstop Technology
- Reliable and Cost Effective Single Die Solution
- Consumer Appliances
- Soft Switching

#### Benefits

- Low Switching Loss Reduces System Power Dissipation

#### Applications

- Inductive Heating

#### Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	$I_C$ Max (A)	$V_{CE(sat)}$ Typ (V)	$V_F$ Typ (V)	$E_{off}$ Typ (mJ)	$E_{on}$ Typ (mJ)	$T_{rr}$ Typ (ns)	$I_T$ Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand ( $\mu$ s)	$E_{AS}$ Typ (mJ)	$P_D$ Max (W)	Co- Pack aged Diode	Pack age Type
NGTB40N120IHRWG	Pb-free Halide free	Active	1200	40	2.3	2.1	0.95	-	-	-	225	-	-	384	Yes	TO-247-3

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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